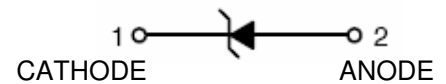
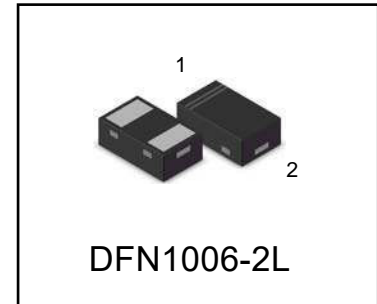


S-BAP64LBS

Planar PIN diode

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low capacitance.
- High voltage, current controlled RF resistor for RF attenuators and switches.
- Low forward resistance.
- Very low series inductance.



2. APPLICATIONS

- RF attenuators and switches.

3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
BAP64LBS	P6	10000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Continuous Reverse Voltage	VR	100	V
Forward Current	IF	100	mA
Total Power Dissipation(Tsp = 90°C)	Ptot	150	mW
Storage temperature	Tstg	-45~+125	°C
Junction temperature	Tj	125	°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Thermal resistance from junction to to solder point	R(θj-sp)	56	K/W

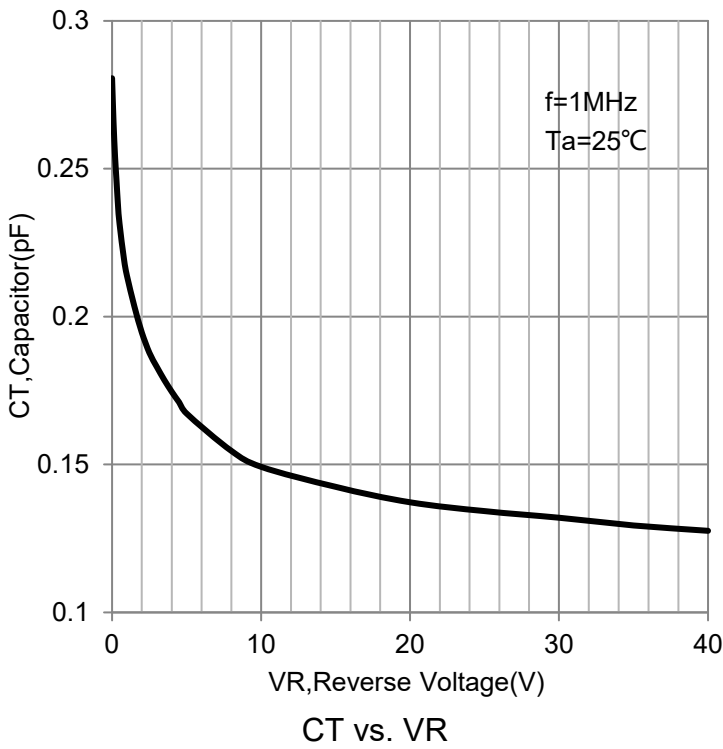
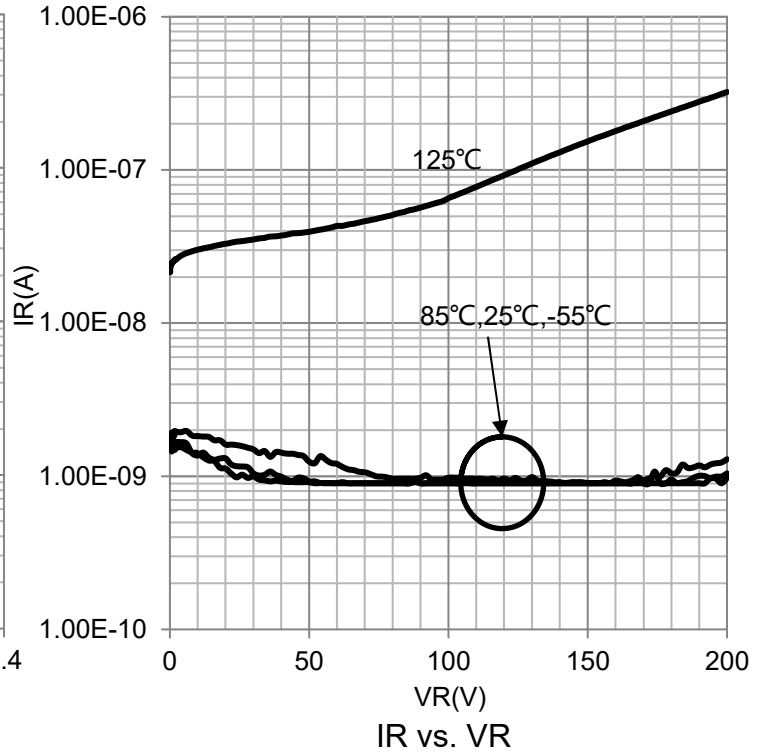
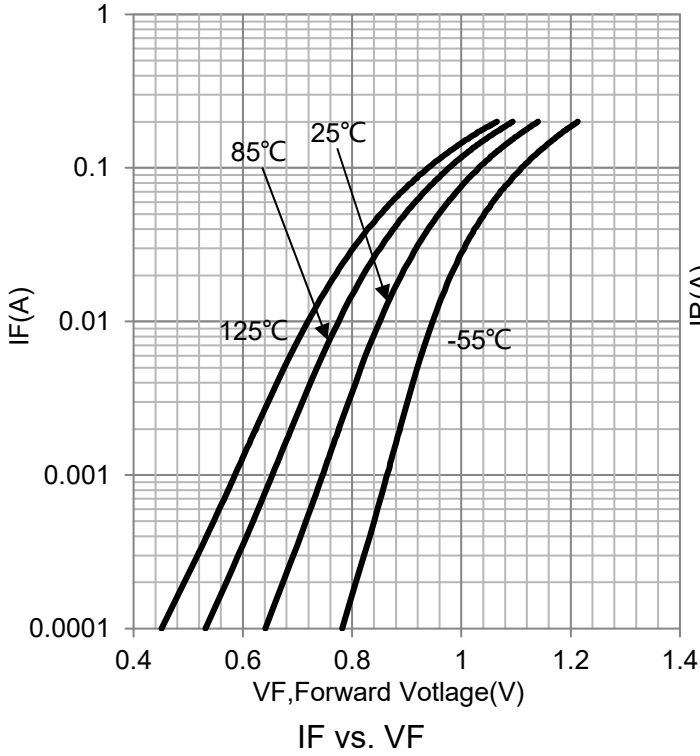


6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

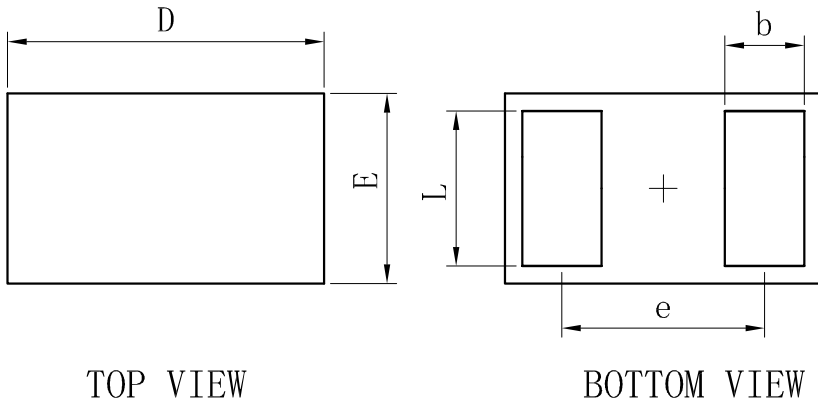
CHARACTERISTICS	Symbol	Min	Typ.	Max	Unit
Continuous Reverse Voltage (IR =10μA)	VR	100	-	-	V
Forward voltage (IF =100mA)	VF	-	0.95	1.1	V
Reverse current (VR=100V)	IR	-	-	300	nA
Diode capacitance (f=1MHz,VR =0V)	Cd	-	0.48	-	pF
(f=1MHz,VR =1V)		-	0.34	-	
(f=1MHz,VR =20V)		-	0.17	0.3	



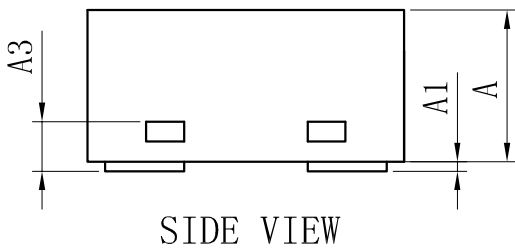
7.ELECTRICAL CHARACTERISTICS CURVES



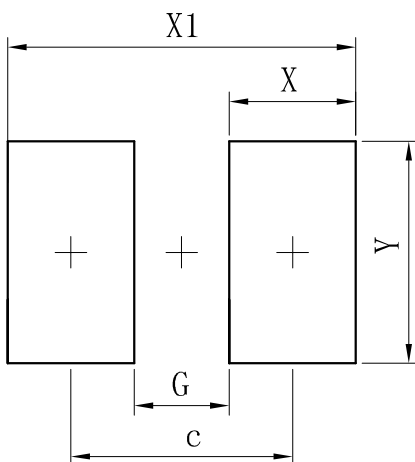
8. OUTLINE AND DIMENSIONS



DFN1006-2L			
Dim	Min	Typ.	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			



9. SOLDERING FOOTPRINT



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

